

General Description

The MAX4885 integrates high-bandwidth analog switches and level-translating buffers to implement a complete 1:2 or 2:1 multiplexer for VGA signals. The device provides switching for RGB, display data channel (DDC), and horizontal and vertical synchronization (HSYNC, VSYNC) signals. A low-noise charge pump with internal capacitors provides a boosted gate-drive voltage to improve performance of the RGB switches.

In the 1:2 multiplexer mode, HSYNC/VSYNC inputs feature level-shifting buffers to support low-voltage CMOS or standard TTL-compatible graphics controllers. In the 2:1 multiplexer mode, the output buffers for the HSYNC/VSYNC inputs are disabled, allowing bidirectional signaling. In both modes, DDC signals are voltage-clamped to an external voltage to provide level translation and protection. The MAX4885 features a 5µA shutdown mode and is ESD protected to ±8kV Human Body Model (HBM) on externally routed pins.

The MAX4885 is specified over the extended (-40°C to +85°C) temperature range, and is available in the 32pin, 5mm x 5mm TQFN package.

Applications

Notebook Computers

Digital Projectors Computer Monitors

Servers

KVM Switches

Features

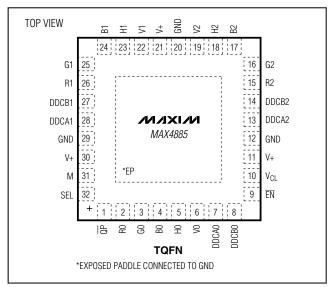
- ♦ +5V Single-Supply Operation
- **♦** Programmable Voltage Clamp for Open-Drain **DDC Signals**
- ♦ Low 5Ω (typ) On-Resistance (R, G, B Signals)
- ♦ Low 13pF (typ) On-Capacitance (R, G, B Signals)
- ♦ Break-Before-Make Switching Protects Against **Circuit Shorts**
- ♦ ±8kV HBM ESD Protection on Externally Routed **Pins**
- ♦ Low 300µA Supply Current (Lower than 1µA with **Charge Pump Disabled)**
- ♦ Space-Saving, Lead-Free, 32-Pin (5mm x 5mm) **TQFN Package**

Ordering Information

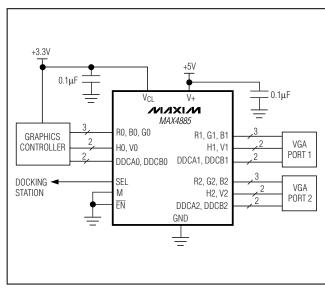
PART	TEMP RANGE	PIN-PACKAGE	PKG CODE
MAX4885ETJ+	-40°C to +85°C	32 TQFN-EP*	T3255-4

^{*}EP = Exposed pad.

Pin Configuration



Typical Operating Circuit



NIXIN

Maxim Integrated Products 1

⁺Denotes lead-free package.

ABSOLUTE MAXIMUM RATINGS

(All voltages referenced to GND.)
V ₊ , V _{CL} 0.3V to +6V
R_, G_, B_, DDCA_, DDCB_, SEL, M,
EN, QP (Note 1)0.3V to V+ + 0.3V
H_, V0.3V to +6V
Continuous Current Through RGB Switches±70mA
Continuous Current Through HV, DDC Switches±50mA
Peak Current Through RGB Switches
(pulsed at 1ms, 10% duty cycle)±140mA
Peak Current Through HV, DDC Switches (pulsed at 1ms,
10% duty cycle)±100mA

Continuous Power Dissipation ($T_A = \frac{1}{2}$	+70°C)
32-Pin TQFN (derate 21.3mW/°C al	bove +70°C)1702mW
Operating Temperature Range	40°C to +85°C
Storage Temperature Range	65°C to +150°C
Junction Temperature	+150°C
Lead Temperature (soldering, 10s)	+300°C

Note 1: Signals exceeding V+ or GND are clamped by internal diodes. Limit forward-diode current to maximum current rating.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

 $(V+ = +5.0V \pm 10\%, V_{CL} = +3.3V \pm 10\%, T_A = T_{MIN} \text{ to } T_{MAX}, \overline{QP} = GND, \text{ unless otherwise noted. Typical values are at } V+ = +5.0V, V_{CL} = +3.3V \text{ and } T_A = +25^{\circ}C.)$

PARAMETER	SYMBOL	CO	NDITIONS	MIN	TYP	MAX	UNITS
Supply Voltage Range	V+			4.5		5.5	V
Clamp Voltage Range	V _{CL}			2.7		V+	V
V Quiescent Supply Current		V+ = +5.5V	QP = GND		0.3	0.5	mA
V ₊ Quiescent Supply Current	I ₊	V+ = +5.5V	$\overline{QP} = V +$			1	μΑ
V _{CL} Quiescent Supply Current	ICL	$V_{CL} = V + = +5.5V$				1	μΑ
V+ Shutdown Current	I+SHDN	V+ = +5.5V, all dig	ital inputs to V+ or GND			5	μΑ
V _{CL} Shutdown Current	ICLSHDN	$V_{CL} = V_{+} = +5.5V,$ GND	all digital inputs to V+ or			1	μΑ
RGB ANALOG SWITCHES							
On Desistance	Davi	$0V < V_{IN} < +2.5V$	QP = GND		5	7.5	0
On-Resistance	Ron	$I_{IN} = -40 \text{mA}$	QP = V+		6	10	Ω
On-Resistance Matching	ΔRon	$0V < V_{IN} < +2.5V$, $I_{IN} = -40$ mA			0.5	1.5	Ω
On-Resistance Flatness	RFLAT(ON)	$0V < V_{IN} < +2.5V$, $I_{IN} = -40$ mA			0.02	0.75	Ω
Off-Leakage Current	I _{L(OFF)}	R_{-} , G_{-} , B_{-} = 0V or +5.5V, \overline{EN} = GND		-1		+1	μΑ
On-Leakage Current	I _L (ON)	R_, G_, B_ = 0V or +5.5V, $\overline{EN} = V+$		-1		+1	μΑ
Charge Injection	Q	R_, G_, B_ = 0V,	$\overline{QP} = GND$		10		200
Charge injection	Q		$\overline{QP} = V +$		8		pC
HV MULTIPLEXER							
Input-Voltage Low	VILHV	M = GND	M = GND			0.8	V
Input-Voltage High	VIHHV	M = GND		2.0			V
High-Output Drive Current	Іонну	V _{OUT} = V ₊ - 0.5V, M = GND		-16			mA
Low-Output Drive Current	lolhv	V _{OUT} = +0.5V, M = GND				+16	mA
On-Resistance	Ronhv	H_ = V_ = +2.5V, I _{IN} = -40mA, M = V+				15	Ω
Charge Injection	Q	H_, V_ = 0V, M = V	'+, C _L = 1000pF		21		рС

ELECTRICAL CHARACTERISTICS (continued)

(V+ = +5.0V \pm 10%, V_{CL} = +3.3V \pm 10%, T_A = T_{MIN} to T_{MAX}, \overline{QP} = GND, unless otherwise noted. Typical values are at V+ = +5.0V, V_{CL} = +3.3V and T_A = +25°C.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
DDC MULTIPLEXER						
On-Resistance	Ron(DDC)	$V_{IN} < +0.4V$, $V_{CL} = +3.0V$, $I_{IN} = -20$ mA			20	Ω
DDC Leakage	I _{L(DDC)}	V_{CL} - 0.4V < V_{OUT} < V_{CL} , V_{IN} = V+	-1		+1	μΑ
Charge Injection	Q	DDCA_, DDCB_ = 0V, CL = 1000pF		10		рС
SWITCH LOGIC (SEL, M, EN, QP)						
Input-Low Voltage	VIL	V+ = +5.5V			0.8	V
Input-High Voltage	VIH	V+ = +4.5V	2.0			V
Input Leakage Current	ILEAK	V _{IN} = V+	-1		+1	μΑ
ESD PROTECTION						
		Human Body Model, all pins		±2		kV
ESD Protection		Human Body Model, R_, G_, B_, H_, V_, DDCA_, DDCB_		±8		kV

AC ELECTRICAL CHARACTERISTICS

 $(V+ = +5.0V \pm 10\%, V_{CL} = +3.3V \pm 10\%, T_A = T_{MIN} \text{ to } T_{MAX}, \overline{QP} = GND.$ Typical values are at $V+ = +5.0V, V_{CL} = +3.3V$ and $T_A = +25^{\circ}C$, unless otherwise noted.) (Note 2)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
Bandwidth	frank	$R_S = R_L = 50\Omega$	$\overline{QP} = GND$		350		MHz
Dariuwiulii	fMAX	LS = LL = SOS2	$\overline{QP} = V +$		350		IVIITZ
Insertion Loss	l. 00	1MHz < f < 50MHz,	$\overline{QP} = GND$		0.85	1.2	dB
Insertion Loss I _{LOS}		$R_S = R_L = 50\Omega$	$\overline{QP} = V +$		1	1.6	ub ub
Crosstalk	V _{CT}	$1 MHz < f < 50 MHz, V_{IN} = 0.7 V_{P-P}, \\ R_S = R_L = 50 \Omega$			-40		dB
Off-Capacitance	Coff	f = 1MHz, $\overline{QP} = GND \text{ or } V+$			5		pF
On-Capacitance	Con	f = 1 MHz	$\overline{QP} = GND$		13		۵۲.
On-Capacitance CON			$\overline{QP} = V +$		17		pF
Charge-Pump Noise	V _{NQP}	$V_{IN} = +1.0V$, $R_S = R_L = 50\Omega$			50	200	μV

TIMING CHARACTERISTICS

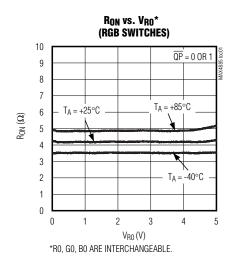
 $(V+ = +5.0V \pm 10\%, V_{CL} = +3.3V \pm 10\%, T_A = T_{MIN} \text{ to } T_{MAX}, \overline{QP} = GND.$ Typical values are at $V+ = +5.0V, V_{CL} = +3.3V$ and $T_A = +25^{\circ}C$, unless otherwise noted.) (Note 2)

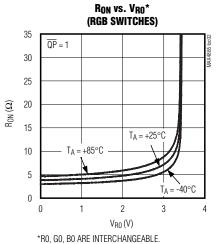
PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
Charge-Pump Startup Time	tqpon				150		μs
RGB ANALOG SWITCHES							
Turn-On Time	ton	$V_{IN} = +1.0V$, $R_L = 100\Omega$, Figure	re 1			7	μs
Turn-Off Time	toff	$V_{IN} = +1.0V$, $R_L = 100\Omega$, Figure	re 1		0.1		μs
Propagation Delay	tpD	$C_L = 10pF$, Figure 2, $R_L = R_S$	= 50Ω		0.1		ns
Output Skew Between Ports	tskew	C_L = 10pF, Skew between any two ports: R, G, B. Figure 2, R_S = R_L = 50Ω			30		ps
HV MULTIPLEXER	•						
Turn-On Time	ton	M = 0, Figure 1				5	μs
Turn-Off Time	toff	M = 0, Figure 1			0.1		μs
Drangation Dalay	+	C. 10°E	M = GND		6	16	50
Propagation Delay	ίΡD	tpD $C_L = 10pF$ $M = V+$		0.1		ns	
DDC MULTIPLEXER							
Turn-On Time	ton	V_{IN} = +1.0V, R_L = 100 Ω , Figure 1				5	μs
Turn-Off Time	toff	V_{IN} = +1.0V, R_L = 100 Ω , Figure 1			0.1		μs
Propagation Delay	t _{PD}	C _L = 10pF, Figure 2			0.25		ns

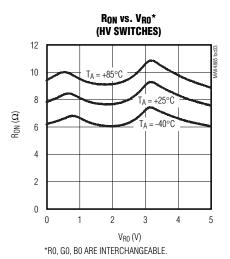
Note 2: Timing parameters are guaranteed by design and correlation over the full operating temperature range.

Typical Operating Characteristics

(V+ = +5.0V, V_{CL} = +3.3V and T_A = +25°C, unless otherwise noted.)

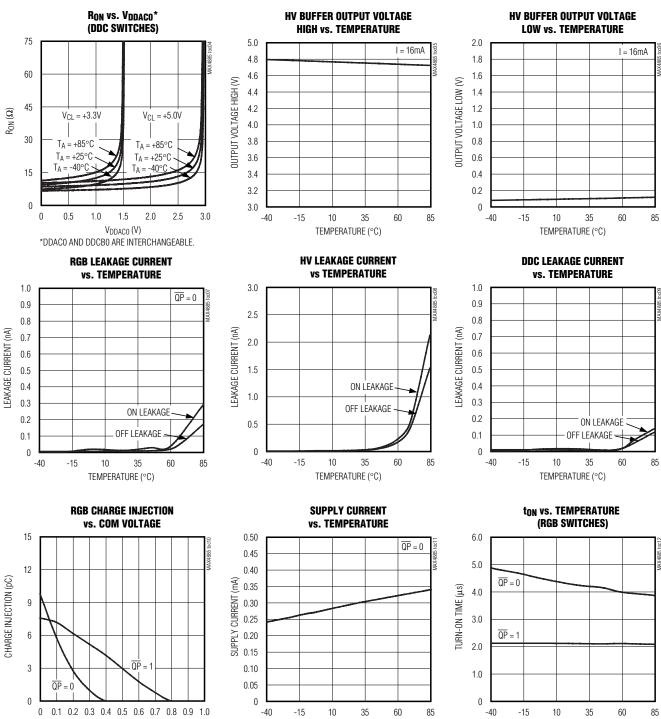






Typical Operating Characteristics (continued)

(V+ = +5.0V, V_{CL} = +3.3V and T_A = +25°C, unless otherwise noted.)



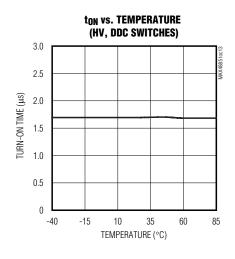
TEMPERATURE (°C)

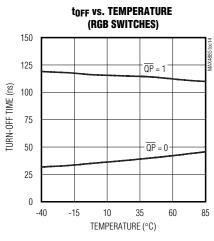
V_{COM} (V)

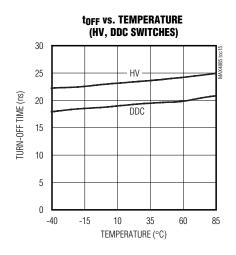
TEMPERATURE (°C)

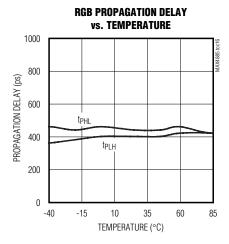
Typical Operating Characteristics (continued)

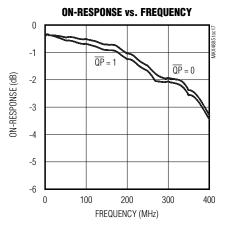
(V+ = +5.0V, V_{CL} = +3.3V and T_A = +25°C, unless otherwise noted.)

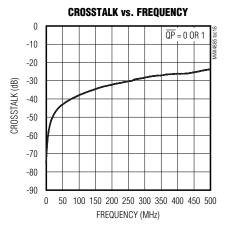


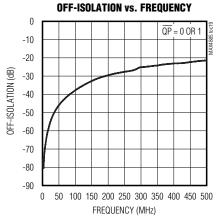












Timing Circuits/Timing Diagrams

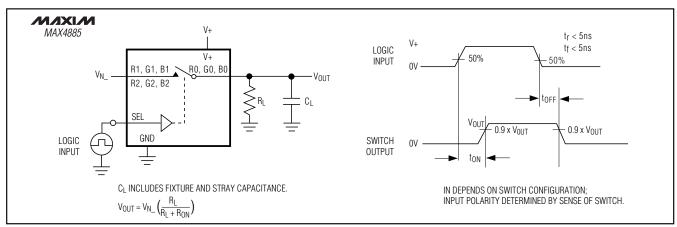


Figure 1. Switching Time

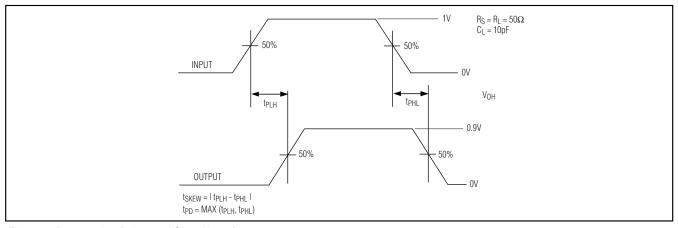


Figure 2. Propagation Delay and Skew Waveforms

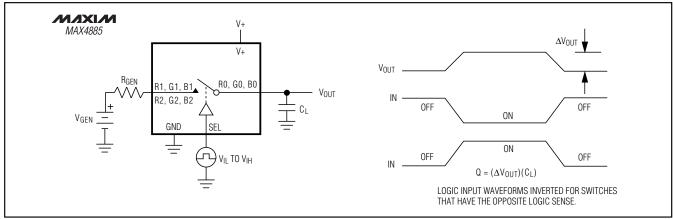


Figure 3. Charge Injection

Timing Circuits/Timing Diagrams (continued)

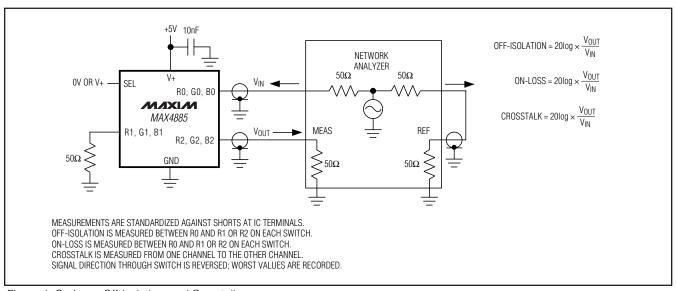


Figure 4. On-Loss, Off-Isolation, and Crosstalk

Pin Description

PIN	NAME	FUNCTION
1	QP	Charge-Pump Enable, Active Low. Drive $\overline{\text{QP}}$ low for normal operation. Drive $\overline{\text{QP}}$ high to disable the internal charge pump.
2	R0	RGB Analog I/O
3	G0	RGB Analog I/O
4	В0	RGB Analog I/O
5	H0	Horizontal Sync I/O
6	V0	Vertical Sync I/O
7	DDCA0	DDC I/O
8	DDCB0	DDC I/O
9	ĒN	Enable Input, Active Low. Drive \overline{EN} low for normal operation. Drive \overline{EN} high to disable the device. All I/Os are high-impedance and charge pump is off when the device is disabled.
10	V _{CL}	DDC Clamp Voltage. Open-drain DDCA_ and DDCB_ outputs are clamped to one diode-drop below V_{CL} . $+2.7V < V_{CL} < V_{+}$. Connect V_{CL} to $+3.3V$ for voltage clamping, or connect to V_{+} to disable clamping. Bypass V_{CL} to GND with a $0.1\mu F$ or larger ceramic capacitor.
11, 21, 30	V+	Supply Voltage. $V+ = +5.0V \pm 10\%$. Bypass each to GND with a $0.1\mu F$ or larger ceramic capacitor.
12, 20, 29	GND	Ground
13	DDCA2	DDC I/O
14	DDCB2	DDC I/O
15	R2	RGB Analog I/O
16	G2	RGB Analog I/O
17	B2	RGB Analog I/O

Pin Description (continued)

PIN	NAME	FUNCTION
18	H2	Horizontal Sync I/O
19	V2	Vertical Sync I/O
22	V1	Vertical Sync I/O
23	H1	Horizontal Sync I/O
24	B1	RGB Analog I/O
25	G1	RGB Analog I/O
26	R1	RGB Analog I/O
27	DDCB1	DDC I/O
28	DDCA1	DDC I/O
31	М	Mode Select. Drive M low for 1:2 multiplexer mode. Drive M high for 2:1 multiplexer mode. See Tables 1, 2, and 3.
32	SEL	Select. Logic input for switching RGB, HV, and DDC switches. See Tables 1, 2, and 3.
EP	EP	Exposed Pad. Connect exposed pad to ground.

Detailed Description

The MAX4885 integrates high-bandwidth analog switches and level-translating buffers to implement a complete 1:2 or 2:1 multiplexer for VGA signals. The device provides switching for RGB, HSYNC, VSYNC, and DDC signals. A low-noise charge pump with internal capacitors provides a boosted gate-drive voltage to improve performance of the RGB switches.

The device provides two modes of operation: 1:2 and 2:1. In 1:2 mode (M = 0), the HSYNC and VSYNC inputs feature level-shifting buffers to support TTL output logic levels from low-voltage graphics controllers. These buffered switches may be driven from as little as $+2.0 \, \text{V}$ up to $+5.5 \, \text{V}$. In 2:1 mode (M=1), the output buffers for the HSYNC and VSYNC signals are disabled. In both modes, RGB signals are routed with the same high-performance analog switches, and DDC signals are voltage clamped to a diode drop less than VCL. Voltage clamping provides protection and compatibility with DDC signals and low-voltage ASICs. In keyboard/video/mouse (KVM) applications, VCL is normally set to $+5 \, \text{V}$ because low-voltage clamping is not required, as specified by the VESA standard.

Drive $\overline{\text{EN}}$ logic high to shut down the MAX4885. In shutdown mode, supply current is reduced to 5µA and all switches are high impedance, providing high-signal rejection. The RGB, HSYNC, VSYNC, and DDC switches are ESD protected to ±8kV by the Human Body Model.

Table 1. RGB Truth Table

ĒN	SEL	FUNCTION
0	0	R0 to R1 G0 to G1 B0 to B1
0	1	R0 to R2 G0 to G2 B0 to B2
1	Х	R_, B_, and G_, High Impedance

X = Don't Care

RGB Switches

The MAX4885 provides three SPDT high-bandwidth switches to route standard VGA R, G, and B signals (see Table 1). A boosted gate-drive voltage is generated by an internal charge pump to improve performance of the RGB switches. The R, G, and B analog switches are identical, and any of the three switches can be used to route red, green, or blue video signals. The RGB switches function with reduced performance with the charge pump disabled.

Charge Pump

A low-noise charge pump with internal capacitors provides a doubled voltage for driving the RGB analog switches. Noise voltage from the charge pump is less than 50µV_{P-P}. The noise level is more than 80dB below the signal level, making the charge pump suitable for

standard VGA signals. The charge pump can be disabled to eliminate charge-pump noise; however, RGB switch performance is slightly degraded. Connect $\overline{\text{QP}}$ to ground for normal operation.

Horizontal/Vertical Sync Multiplexer

1:2 Multiplexer Mode

The MAX4885 provides two modes of operation for the HSYNC and VSYNC signals. In 1:2 mode (M = 0), the HSYNC/VSYNC inputs are buffered to provide level shifting and drive capability to meet the VESA specification.

2:1 Multiplexer Mode

In 2:1 mode (M = 1), the HSYNC/VSYNC output buffers are disabled, and switches pass signals directly. The HSYNC and VSYNC switches/buffers are identical, and either input can be used to route HSYNC and VSYNC signals.

Display Data Channel Multiplexer

The MAX4885 provides two voltage-clamped switches to route DDC signals (see Table 3). Each switch clamps signals to a diode drop less than the voltage applied on VCL. Supply +3.3V on VCL to provide voltage clamping for VESA I²C-compatible signals. If voltage clamping is not required, connect VCL to V+. The DDCA and DDCB switches are identical, and each switch can be used to route either DDC signal.

ESD Protection

As with all Maxim devices, ESD-protection structures are incorporated on all pins to protect against electrostatic discharges encountered during handling and assembly. Additionally, the MAX4885 is protected to ±8kV on RGB, HSYNC, VSYNC, and DDC switches by the Human Body Model (HBM). For optimum ESD performance, bypass each V+ pin to ground with a 0.1µF or larger ceramic capacitor.

Human Body Model (HBM)

Several ESD testing standards exist for measuring the robustness of ESD structures. The ESD protection of the MAX4885 is characterized with the Human Body Model. Figure 5 shows the model used to simulate an ESD event resulting from contact with the human body. The model consists of a 100pF storage capacitor that is charged to a high voltage, then discharged through a 1.5k Ω resistor. Figure 6 shows the current waveform when the storage capacitor is discharged into a low impedance.

ESD Test Conditions

ESD performance depends on a variety of conditions. Please contact Maxim for a reliability report documenting test setup, methodology, and results.

Table 2. HV Truth Table

EN	М	SEL	FUNCTION
0	0	0	1:2 Mode Buffers Enabled H0 to H1 V0 to V1
0	0	1	1:2 Mode Buffers Enabled H0 to H2 V0 to V2
0	1	0	2:1 Mode Buffers Disabled H0 to H1 V0 to V1
0	1	1	2:1 Mode Buffers Disabled H0 to H2 V0 to V2
1	×	Х	H_, V_ High Impedance

X = Don't Care

Table 3. DDC Truth Table

ĒN	SEL	FUNCTION
0	0	DDCA0 to DDCA1 DDCB0 to DDCB1
0	1	DDCA0 to DDCA2 DDCB0 to DDCB2
1	Х	DDCA_, DDCB_ High Impedance

X = Don't Care

_Applications Information

1:2 Multiplexer for Low-Voltage Graphics Controllers

The MAX4885 provides the level shifting necessary to drive two standard VGA ports from a graphics controller as low as +2.2V. In 1:2 mode, internal buffers drive the HSYNC and VSYNC signals to VGA standard TTL levels. The DDC multiplexer provides level shifting by clamping signals to a diode drop less than V_{CL} (see the *Typical Operating Circuit*). Connect V_{CL} to +3.3V for normal operation, or to V+ to disable voltage clamping for DDC signals.

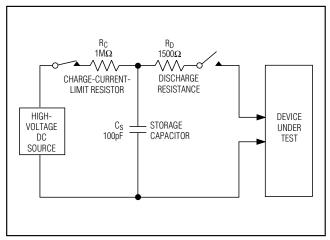


Figure 5. Human Body ESD Test Model

2:1 Multiplexer

In 2:1 mode, HSYNC and VSYNC buffers are disabled, allowing bidirectional signaling. The DDC multiplexer provides level shifting by clamping signals to a diode drop less than V_{CL} (see the *Typical Operating Circuit*). Connect V_{CL} to V+ to disable voltage clamping for DDC signals.

Power-Supply Decoupling

Bypass each V+ pin and V_{CL} to ground with a $0.1\mu F$ or larger ceramic capacitor as close to the device as possible.

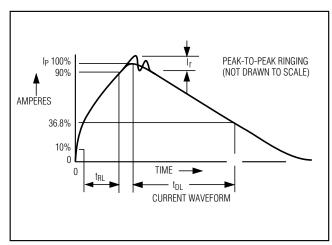


Figure 6. HBM Discharge Current Waveform

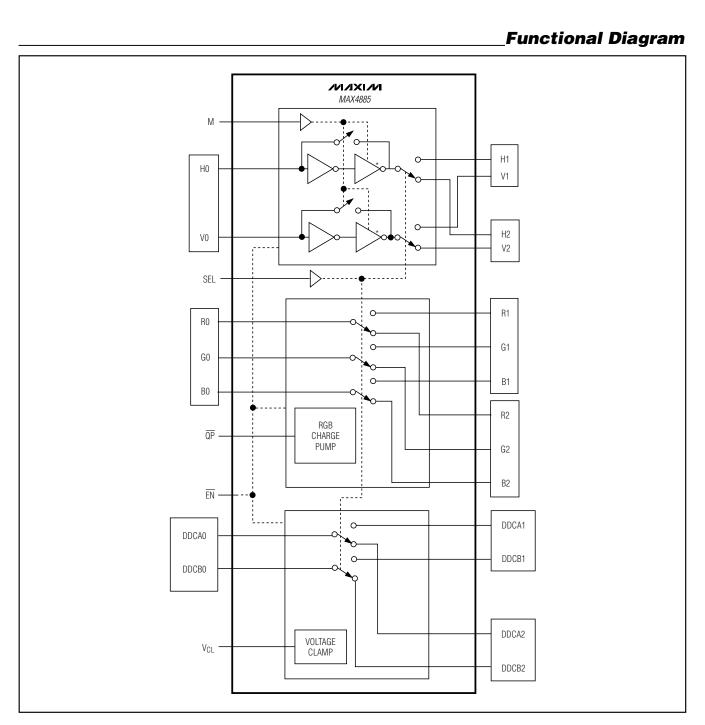
PC Board Layout

High-speed switches such as the MAX4885 require proper PC board layout for optimum performance. Ensure that impedance-controlled PC board traces for high-speed signals are matched in length and as short as possible. Connect the exposed pad to a solid ground plane.

Chip Information

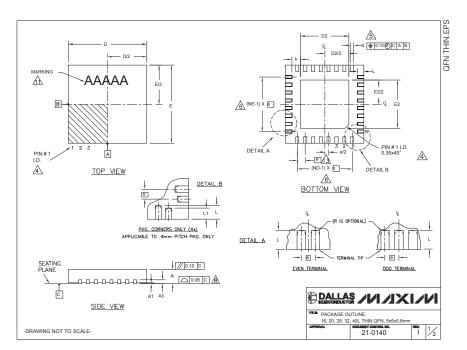
PROCESS: BICMOS

CONNECT EXPOSED PAD TO GND



Package Information

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information, go to www.maxim-ic.com/packages.)



			С	OMMO	D NC	IMEN	SION	S										EXI	POSE	D PAD	VARI	ATION	S		
PKG.	16L 5x5			20L 5x5			28L 5x5			32L 5x5			40L 5x5]	PKG.	D2			E2			L	DOWN	
SYMBOL	=							NOM.		-	-	_	-		-	4	CODES	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	±0.15	BONDS ALLOWED
Α	-	0.75		-	-		-	_		-	0.75		-	-	-	1	T1655-2	3.00	3.10	3.20	3.00	3.10	3.20	**	YES
A1	0	0.02		_	0.02		_	_	0.05	0	0.02		_		0.05	4	T1655-3	3.00	3.10	3.20	3.00	3.10	3.20	**	NO
A3	0.20 REF.		0.20 REF.		0.20 REF.		0.20 REF.		0.20 REF.		1	T1655N-1	3.00	3.10	3.20	3.00	3.10	3.20	**	NO					
b								0.25						0		1	T2055-3	3.00	3.10	3.20	3.00	3.10	3.20	**	YES
D F		5.00		4.90							5.00					4	T2055-4	3.00	3.10	3.20	3.00	3.10	3.20	**	NO
		5.00 80 B		4.90	5.00 65 B			50 BS		4.90	5.00 50 BS			5.00 40 B		4	T2055-5	3.15	3 25	3.35	3.15	3.25	3.35	0.40	YES
e k	0.25	1.80 B	SC.	0.25	65 B	SC.	0.25	.50 BS	iC.	0.25	.50 BS	SG.	-		0.45	1	T2855-3	3.15	3.25	3.35	3.15	3.25	3.35	**	YES
I I		-		_	-	- 0.05	_	-	0.05	_	-	0.50	_		_	1	T2855-4	2.60	2.70	2.80	2.60	2.70	2.80	**	YES
11	0.30	0.40	0.50	0.45	0.55	0.65	0.45	0.55	0.65	0.30	0.40	0.50	0.40	0.50	0.60	Ψ.	T2855-5	2.60	2.70	2.80	2.60	2.70	2.80	**	NO
N	<u> </u>	16	-	1	20	-	<u> </u>	28	-	÷	32	-	0.30	40	10.50	1	T2855-6	3.15	3.25	3.35	3.15	3.25	3.35	**	NO
ND	4		5		7		8		10		1	T2855-7	2.60	2.70	2.80	2.60	2.70	2.80	**	YES					
NE	-	4		5			7			8				10		1	T2855-8	3.15	3 25	3.35	3.15	3.25	3.35	0.40	YES
JEDEC	EDEC WHHB			WHHC			WHHD-1			V	WHHD-2				T2855N-1	3.15	3.25	3.35	3.15	3.25	3.35	**	NO		
																-	T3255-3	3.00	3.10	3.20	3.00	3.10	3.20	**	YES
OTES:																	T3255-4	3.00	3.10	3.20	3.00	3.10	3.20	**	NO
	DIMENSIONING & TOLERANCING CONFORM TO ASME Y14.5M-1994.											T3255-5	3.00	3.10	3.20	3.00	3.10	3.20	**	YES					
2 ALI	DIME	NSIO	NS AF	RE IN I	MILLI	METE	RS A	NGI ES	SARE	IN D	FGRE	FS					T3255N-1	3.00	3.10	3.20	3.00	3.10	3.20	**	NO
3. N IS	THE	TOTA	NUM	MRER	OF T	ERMI	VΔI S										T4055-1	3.20	3.30	3.40	3.20	3.30	3.40	**	YES
OP* IDE DIN 0.25	NFOR TIONA NTIFI IENSI 5 mm	M TO L, BU ER MA ON b A AND 0	JESD T MUS Y BE APPLII .30 m	95-1 S ST BE EITHE ES TO m FRO	SPP-0 LOC/ ER A I MET OM TE	ATED MOLD ALLIZ RMIN	WITH OR N ED TE	S OF IN THE IARKE ERMIN P.	TERM ZON D FE	MINAL NE INE ATUR ND IS	#1 ID DICATI E. MEAS	ENTII ED. T	HE TE	ARE RMIN	NAL#										
								ERMIN				ANE	DE SI	DE RI	ESPE	CTIVE	LY.								
7. DEF																									
								HEA.								NALS									
9. DR/		3 CON AND T			JEDI	EC M	0220,	EXCE	PT E)	(POS	ED PA	D DI	MENS	ION F	OR			_							
<u>∕10.</u> wa	RPAC	E SHA	ALL N	OT EX	CEE	0.10	mm.											1	αAi	ALL	AS	41	4		
11. MA	RKIN	SISF	OR PA	CKAG	SE OF	RIENT	ATION	REFE	REN	CE O	NLY.							Į.	'I' = 5	NICOND	UCTOR	N W			
	MBER	OF L	EADS	SHOV	VN AF	RE FO	R REI	FEREN	ICE (NLY.								H	mus p	VCK VC	SE OUT	TIME			
12. NUI		NITED	INIES	TOB	FΔT	TRUE	POS	ITION.	AS D	EFINE	D BY	BASI	C DIM	ENSI	ON "e	", ±0.0)5.						N OFN	5x5x0.8	mm
Α .	AD CE	NIER																							
Α .																		F	APPROVAL			CUMENT O			REV.

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